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### Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

### Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	516096
Number of I/O	620
Number of Gates	3000000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	896-BGA
Supplier Device Package	896-FBGA (31x31)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/microchip-technology/m1a3pe3000-fgg896i">https://www.e-xfl.com/product-detail/microchip-technology/m1a3pe3000-fgg896i</a>

## **Single Chip**

Flash-based FPGAs store their configuration information in on-chip flash cells. Once programmed, the configuration data is an inherent part of the FPGA structure, and no external configuration data needs to be loaded at system power-up (unlike SRAM-based FPGAs). Therefore, flash-based ProASIC3E FPGAs do not require system configuration components such as EEPROMs or microcontrollers to load device configuration data. This reduces bill-of-materials costs and PCB area, and increases security and system reliability.

## **Instant On**

Flash-based ProASIC3E devices support Level 0 of the Instant On classification standard. This feature helps in system component initialization, execution of critical tasks before the processor wakes up, setup and configuration of memory blocks, clock generation, and bus activity management. The Instant On feature of flash-based ProASIC3E devices greatly simplifies total system design and reduces total system cost, often eliminating the need for CPLDs and clock generation PLLs that are used for these purposes in a system. In addition, glitches and brownouts in system power will not corrupt the ProASIC3E device's flash configuration, and unlike SRAM-based FPGAs, the device will not have to be reloaded when system power is restored. This enables the reduction or complete removal of the configuration PROM, expensive voltage monitor, brownout detection, and clock generator devices from the PCB design. Flash-based ProASIC3E devices simplify total system design and reduce cost and design risk while increasing system reliability and improving system initialization time.

## **Firm Errors**

Firm errors occur most commonly when high-energy neutrons, generated in the upper atmosphere, strike a configuration cell of an SRAM FPGA. The energy of the collision can change the state of the configuration cell and thus change the logic, routing, or I/O behavior in an unpredictable way. These errors are impossible to prevent in SRAM FPGAs. The consequence of this type of error can be a complete system failure. Firm errors do not exist in the configuration memory of ProASIC3E flash-based FPGAs. Once it is programmed, the flash cell configuration element of ProASIC3E FPGAs cannot be altered by high-energy neutrons and is therefore immune to them. Recoverable (or soft) errors occur in the user data SRAM of all FPGA devices. These can easily be mitigated by using error detection and correction (EDAC) circuitry built into the FPGA fabric.

## **Low Power**

Flash-based ProASIC3E devices exhibit power characteristics similar to an ASIC, making them an ideal choice for power-sensitive applications. ProASIC3E devices have only a very limited power-on current surge and no high-current transition period, both of which occur on many FPGAs.

ProASIC3E devices also have low dynamic power consumption to further maximize power savings.

## **Advanced Flash Technology**

The ProASIC3E family offers many benefits, including nonvolatility and reprogrammability through an advanced flash-based, 130-nm LVCMOS process with seven layers of metal. Standard CMOS design techniques are used to implement logic and control functions. The combination of fine granularity, enhanced flexible routing resources, and abundant flash switches allows for very high logic utilization without compromising device routability or performance. Logic functions within the device are interconnected through a four-level routing hierarchy.

## Calculating Power Dissipation

### Quiescent Supply Current

**Table 2-7 • Quiescent Supply Current Characteristics**

	A3PE600	A3PE1500	A3PE3000
Typical (25°C)	5 mA	12 mA	25 mA
Maximum (Commercial)	30 mA	70 mA	150 mA
Maximum (Industrial)	45 mA	105 mA	225 mA

**Notes:**

1. *IDD* Includes *VCC*, *VPUMP*, *VCCI*, and *VMV* currents. Values do not include I/O static contribution, which is shown in [Table 2-8](#) and [Table 2-9](#) on [page 2-7](#).
2. *-F* speed grade devices may experience higher standby *IDD* of up to five times the standard *IDD* and higher I/O leakage.

### Power per I/O Pin

**Table 2-8 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings**

	VMV (V)	Static Power PDC2 (mW) <sup>1</sup>	Dynamic Power PAC9 (μW/MHz) <sup>2</sup>
<b>Single-Ended</b>			
3.3 V LVTTTL/LVCMOS	3.3	–	17.39
3.3 V LVTTTL/LVCMOS – Schmitt trigger	3.3	–	25.51
3.3 V LVTTTL/LVCMOS Wide Range <sup>3</sup>	3.3	–	16.34
3.3 V LVTTTL/LVCMOS Wide Range – Schmitt trigger <sup>3</sup>	3.3	–	24.49
2.5 V LVCMOS	2.5	–	5.76
2.5 V LVCMOS – Schmitt trigger	2.5	–	7.16
1.8 V LVCMOS	1.8	–	2.72
1.8 V LVCMOS – Schmitt trigger	1.8	–	2.80
1.5 V LVCMOS (JESD8-11)	1.5	–	2.08
1.5 V LVCMOS (JESD8-11) – Schmitt trigger	1.5	–	2.00
3.3 V PCI	3.3	–	18.82
3.3 V PCI – Schmitt trigger	3.3	–	20.12
3.3 V PCI-X	3.3	–	18.82
3.3 V PCI-X – Schmitt trigger	3.3	–	20.12
<b>Voltage-Referenced</b>			
3.3 V GTL	3.3	2.90	8.23
2.5 V GTL	2.5	2.13	4.78
3.3 V GTL+	3.3	2.81	4.14
2.5 V GTL+	2.5	2.57	3.71

**Notes:**

1. *PDC2* is the static power (where applicable) measured on *VMV*.
2. *PAC9* is the total dynamic power measured on *VCC* and *VMV*.
3. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8b specification.

## Single-Ended I/O Characteristics

### 3.3 V LVTTTL / 3.3 V LVCMOS

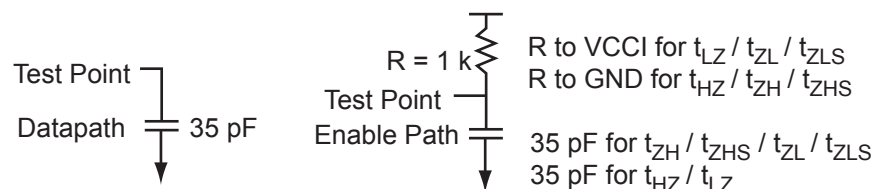
Low-Voltage Transistor–Transistor Logic is a general-purpose standard (EIA/JESD) for 3.3 V applications. It uses an LVTTTL input buffer and push-pull output buffer. The 3.3 V LVCMOS standard is supported as part of the 3.3 V LVTTTL support.

**Table 2-25 • Minimum and Maximum DC Input and Output Levels**

3.3 V LVTTTL / 3.3 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL <sup>1</sup>	IIH <sup>2</sup>
Drive Strength	Min. V	Max. V	Min., V	Max. V	Max. V	Min. V	mA	mA	Max. mA <sup>3</sup>	Max. mA <sup>3</sup>	μA <sup>4</sup>	μA <sup>4</sup>
2 mA	−0.3	0.8	2	3.6	0.4	2.4	4	4	27	25	10	10
4 mA	−0.3	0.8	2	3.6	0.4	2.4	4	4	27	25	10	10
6 mA	−0.3	0.8	2	3.6	0.4	2.4	8	8	54	51	10	10
8 mA	−0.3	0.8	2	3.6	0.4	2.4	8	8	54	51	10	10
12 mA	−0.3	0.8	2	3.6	0.4	2.4	12	12	109	103	10	10
16 mA	−0.3	0.8	2	3.6	0.4	2.4	16	16	127	132	10	10
24 mA	−0.3	0.8	2	3.6	0.4	2.4	24	24	181	268	10	10

**Notes:**

1. IIL is the input leakage current per I/O pin over recommended operation conditions where  $-0.3\text{ V} < V_{IN} < V_{IL}$ .
2. IIH is the input leakage current per I/O pin over recommended operating conditions  $V_{IH} < V_{IN} < V_{CCI}$ . Input current is larger when operating outside recommended ranges.
3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.



**Figure 2-6 • AC Loading**

**Table 2-26 • 3.3 V LVTTTL / 3.3 V LVCMOS AC Waveforms, Measuring Points, and Capacitive Loads**

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	C <sub>LOAD</sub> (pF)
0	3.3	1.4	–	35

**Note:** \*Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.



## 1.5 V LVCMOS (JESD8-11)

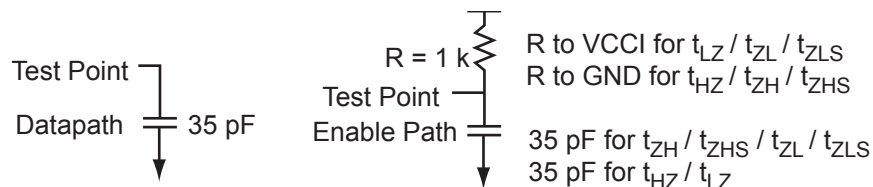
Low-Voltage CMOS for 1.5 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 1.5 V applications. It uses a 1.5 V input buffer and a push-pull output buffer.

**Table 2-41 • Minimum and Maximum DC Input and Output Levels**

1.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL <sup>1</sup>	IIH <sup>2</sup>
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA <sup>3</sup>	Max. mA <sup>3</sup>	μA <sup>4</sup>	μA <sup>4</sup>
2 mA	−0.3	0.30 * VCCI	0.7 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2	16	13	10	10
4 mA	−0.3	0.30 * VCCI	0.7 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	4	4	33	25	10	10
6 mA	−0.3	0.30 * VCCI	0.7 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	6	6	39	32	10	10
8 mA	−0.3	0.30 * VCCI	0.7 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	8	8	55	66	10	10
12 mA	−0.3	0.30 * VCCI	0.7 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	12	12	55	66	10	10

**Notes:**

1. IIL is the input leakage current per I/O pin over recommended operation conditions where  $-0.3\text{ V} < V_{IN} < V_{IL}$ .
2. IIH is the input leakage current per I/O pin over recommended operating conditions  $V_{IH} < V_{IN} < V_{CCI}$ . Input current is larger when operating outside recommended ranges.
3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.



**Figure 2-10 • AC Loading**

**Table 2-42 • AC Waveforms, Measuring Points, and Capacitive Loads**

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	C <sub>LOAD</sub> (pF)
0	1.5	0.75	—	35

**Note:** \*Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.

### 3.3 V PCI, 3.3 V PCI-X

Peripheral Component Interface for 3.3 V standard specifies support for 33 MHz and 66 MHz PCI Bus applications.

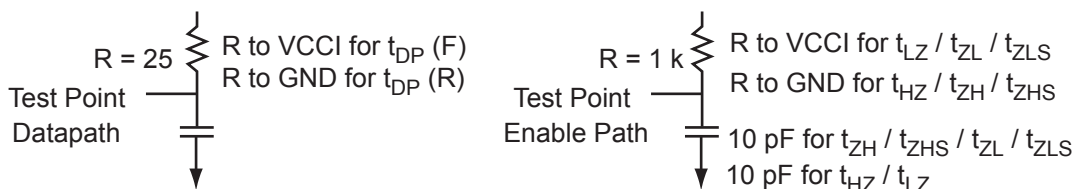
**Table 2-45 • Minimum and Maximum DC Input and Output Levels**

3.3 V PCI/PCI-X	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL <sup>1</sup>	IIH <sup>2</sup>
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA <sup>3</sup>	Max. mA <sup>3</sup>	μA <sup>4</sup>	μA <sup>4</sup>
Per PCI specification	Per PCI curves										10	10

**Notes:**

1. IIL is the input leakage current per I/O pin over recommended operation conditions where  $-0.3\text{ V} < V_{IN} < V_{IL}$ .
2. IIH is the input leakage current per I/O pin over recommended operating conditions  $V_{IH} < V_{IN} < V_{CCI}$ . Input current is larger when operating outside recommended ranges.
3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
4. Currents are measured at 85°C junction temperature.

AC loadings are defined per the PCI/PCI-X specifications for the datapath; Microsemi loadings for enable path characterization are described in [Figure 2-11](#).



**Figure 2-11 • AC Loading**

AC loadings are defined per PCI/PCI-X specifications for the datapath; Microsemi loading for tristate is described in [Table 2-46](#).

**Table 2-46 • AC Waveforms, Measuring Points, and Capacitive Loads**

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	C <sub>LOAD</sub> (pF)
0	3.3	0.285 * VCCI for t <sub>DP(R)</sub> 0.615 * VCCI for t <sub>DP(F)</sub>	—	10

**Note:** \*Measuring point = Vtrip. See [Table 2-15 on page 2-18](#) for a complete table of trip points.

### Timing Characteristics

**Table 2-47 • 3.3 V PCI/PCI-X**

Commercial-Case Conditions: T<sub>J</sub> = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Speed Grade	t <sub>DOUT</sub>	t <sub>DP</sub>	t <sub>DIN</sub>	t <sub>PY</sub>	t <sub>PYS</sub>	t <sub>EOUT</sub>	t <sub>ZL</sub>	t <sub>ZH</sub>	t <sub>LZ</sub>	t <sub>HZ</sub>	t <sub>ZLS</sub>	t <sub>ZHS</sub>	Units
Std.	0.66	2.81	0.04	1.05	1.67	0.43	2.86	2.00	3.28	3.61	5.09	4.23	ns
–1	0.56	2.39	0.04	0.89	1.42	0.36	2.43	1.70	2.79	3.07	4.33	3.60	ns
–2	0.49	2.09	0.03	0.78	1.25	0.32	2.13	1.49	2.45	2.70	3.80	3.16	ns

**Note:** For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-5](#) for derating values.

## SSTL2 Class I

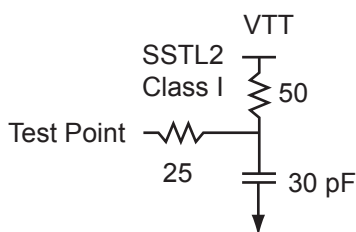
Stub-Speed Terminated Logic for 2.5 V memory bus standard (JESD8-9). ProASIC3E devices support Class I. This provides a differential amplifier input buffer and a push-pull output buffer.

**Table 2-66 • Minimum and Maximum DC Input and Output Levels**

SSTL2 Class I	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA <sup>1</sup>	Max. mA <sup>1</sup>	μA <sup>2</sup>	μA <sup>2</sup>
15 mA	−0.3	VREF − 0.2	VREF + 0.2	3.6	0.54	VCCI − 0.62	15	15	87	83	10	10

**Notes:**

1. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
2. Currents are measured at 85°C junction temperature.



**Figure 2-18 • AC Loading**

**Table 2-67 • AC Waveforms, Measuring Points, and Capacitive Loads**

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C <sub>LOAD</sub> (pF)
VREF − 0.2	VREF + 0.2	1.25	1.25	1.25	30

**Note:** \*Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.

## Timing Characteristics

**Table 2-68 • SSTL 2 Class I**

Commercial-Case Conditions: T<sub>J</sub> = 70°C, Worst-Case VCC = 1.425 V,  
Worst-Case VCCI = 2.3 V, VREF = 1.25 V

Speed Grade	t <sub>DOUT</sub>	t <sub>DP</sub>	t <sub>DIN</sub>	t <sub>PY</sub>	t <sub>EOUT</sub>	t <sub>ZL</sub>	t <sub>ZH</sub>	t <sub>LZ</sub>	t <sub>HZ</sub>	t <sub>ZLS</sub>	t <sub>ZHS</sub>	Units
Std.	0.66	2.13	0.04	1.33	0.43	2.17	1.85			4.40	4.08	ns
−1	0.56	1.81	0.04	1.14	0.36	1.84	1.57			3.74	3.47	ns
−2	0.49	1.59	0.03	1.00	0.32	1.62	1.38			3.29	3.05	ns

**Note:** For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

**Table 2-78 • LVDS Minimum and Maximum DC Input and Output Levels**

DC Parameter	Description	Min.	Typ.	Max.	Units
VCCI	Supply Voltage	2.375	2.5	2.625	V
VOL	Output Low Voltage	0.9	1.075	1.25	V
VOH	Output High Voltage	1.25	1.425	1.6	V
IOL <sup>1</sup>	Output Lower Current	0.65	0.91	1.16	mA
IOH <sup>1</sup>	Output High Current	0.65	0.91	1.16	mA
VI	Input Voltage	0		2.925	V
IIH <sup>2</sup>	Input High Leakage Current			10	μA
IIL <sup>2</sup>	Input Low Leakage Current			10	μA
VODIFF	Differential Output Voltage	250	350	450	mV
VOCM	Output Common Mode Voltage	1.125	1.25	1.375	V
VICM	Input Common Mode Voltage	0.05	1.25	2.35	V
VIDIFF	Input Differential Voltage <sup>2</sup>	100	350		mV

**Notes:**

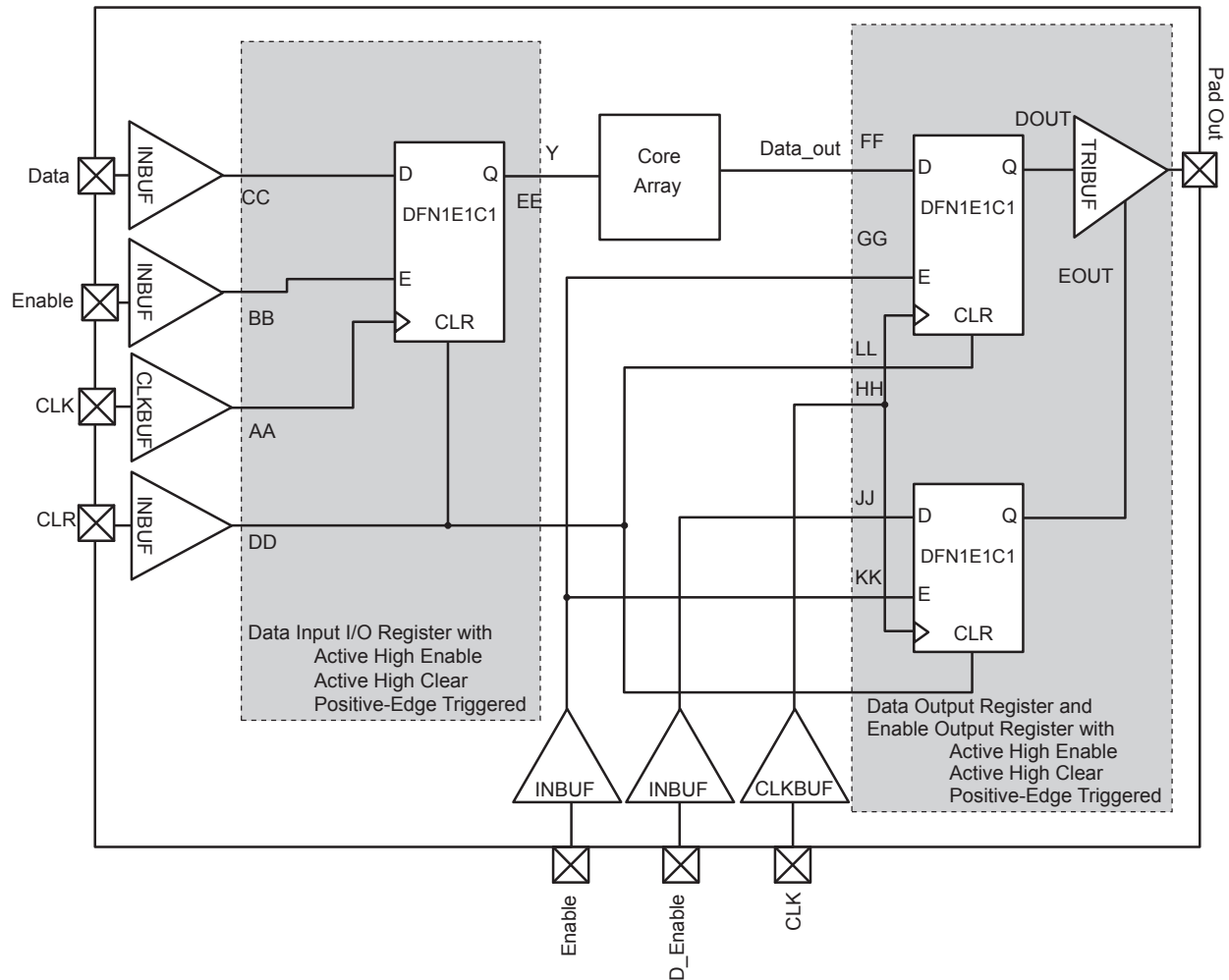
1. IOL/IOH defined by VODIFF/(Resistor Network).
2. Currents are measured at 85°C junction temperature.

**Table 2-79 • AC Waveforms, Measuring Points, and Capacitive Loads**

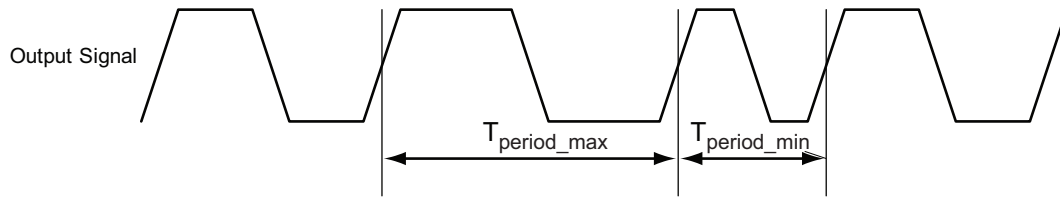
Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)
1.075	1.325	Cross point	–

**Note:** \*Measuring point = Vtrip. See [Table 2-15 on page 2-18](#) for a complete table of trip points.

## Fully Registered I/O Buffers with Synchronous Enable and Asynchronous Clear

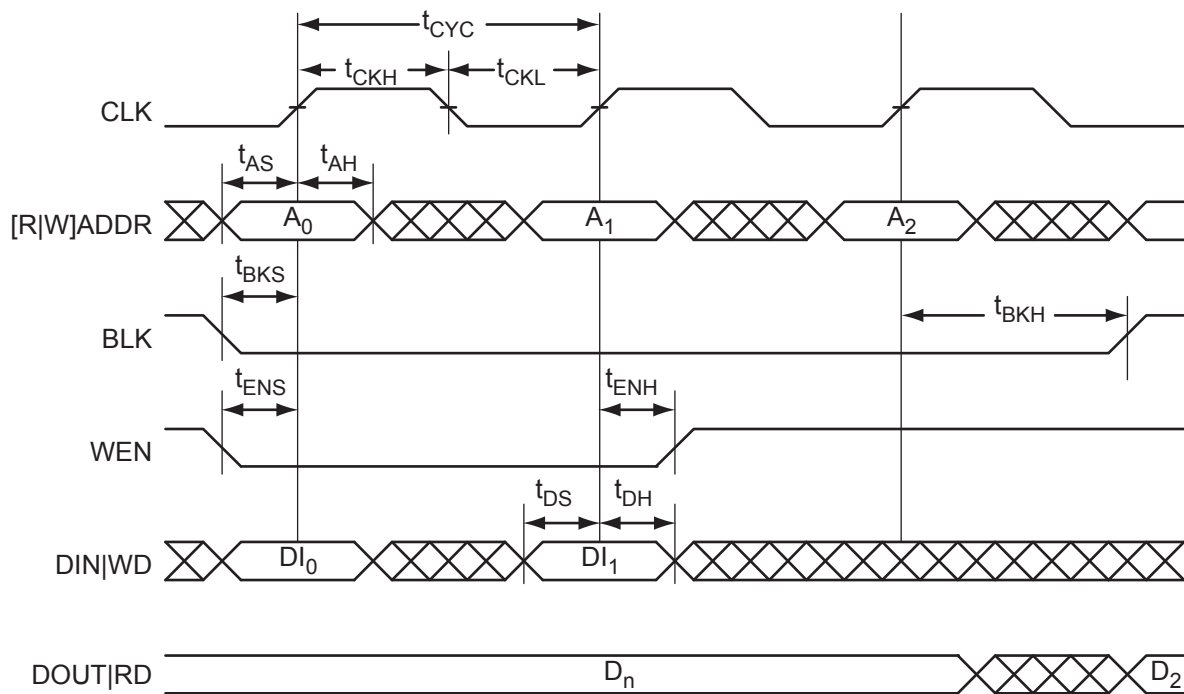


**Figure 2-26 • Timing Model of the Registered I/O Buffers with Synchronous Enable and Asynchronous Clear**

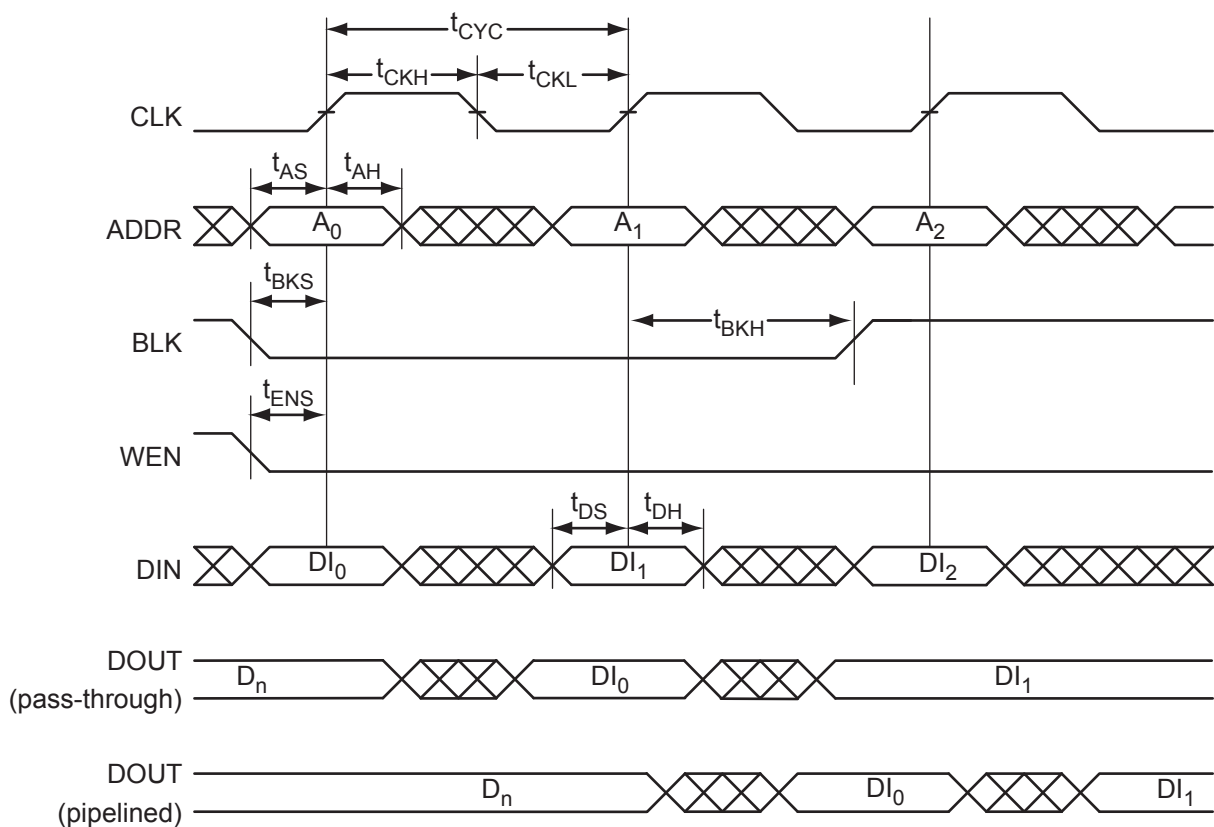


*Note:* Peak-to-peak jitter measurements are defined by  $T_{\text{peak-to-peak}} = T_{\text{period\_max}} - T_{\text{period\_min}}$ .

**Figure 2-39 • Peak-to-Peak Jitter Definition**



**Figure 2-43 • RAM Write, Output Retained. Applicable to Both RAM4K9 and RAM512x18.**



**Figure 2-44 • RAM Write, Output as Write Data. Applicable to RAM4K9 Only.**

## Timing Characteristics

**Table 2-99 • RAM4K9**

Commercial-Case Conditions:  $T_J = 70^{\circ}\text{C}$ , Worst-Case  $V_{CC} = 1.425\text{ V}$ 

Parameter	Description	–2	–1	Std.	Units
$t_{AS}$	Address setup time	0.25	0.28	0.33	ns
$t_{AH}$	Address hold time	0.00	0.00	0.00	ns
$t_{ENS}$	REN, WEN setup time	0.14	0.16	0.19	ns
$t_{ENH}$	REN, WEN hold time	0.10	0.11	0.13	ns
$t_{BKS}$	BLK setup time	0.23	0.27	0.31	ns
$t_{BKH}$	BLK hold time	0.02	0.02	0.02	ns
$t_{DS}$	Input data (DIN) setup time	0.18	0.21	0.25	ns
$t_{DH}$	Input data (DIN) hold time	0.00	0.00	0.00	ns
$t_{CKQ1}$	Clock High to new data valid on DOUT (output retained, WMODE = 0)	1.79	2.03	2.39	ns
	Clock High to new data valid on DOUT (flow-through, WMODE = 1)	2.36	2.68	3.15	ns
$t_{CKQ2}$	Clock High to new data valid on DOUT (pipelined)	0.89	1.02	1.20	ns
$t_{C2CWWL}^1$	Address collision clk-to-clk delay for reliable write after write on same address—Applicable to Closing Edge	0.33	0.28	0.25	ns
$t_{C2CWWH}^1$	Address collision clk-to-clk delay for reliable write after write on same address—Applicable to Rising Edge	0.30	0.26	0.23	ns
$t_{C2CRWH}^1$	Address collision clk-to-clk delay for reliable read access after write on same address—Applicable to Opening Edge	0.45	0.38	0.34	ns
$t_{C2CWRH}^1$	Address collision clk-to-clk delay for reliable write access after read on same address—Applicable to Opening Edge	0.49	0.42	0.37	ns
$t_{RSTBQ}$	RESET Low to data out Low on DO (flow-through)	0.92	1.05	1.23	ns
	RESET Low to Data Out Low on DO (pipelined)	0.92	1.05	1.23	ns
$t_{REMRSTB}$	RESET removal	0.29	0.33	0.38	ns
$t_{RECRSTB}$	RESET recovery	1.50	1.71	2.01	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.21	0.24	0.29	ns
$t_{CYC}$	Clock cycle time	3.23	3.68	4.32	ns
$F_{MAX}$	Maximum frequency	310	272	231	MHz

### Notes:

1. For more information, refer to the application note [Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs](#).
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-5](#) for derating values.

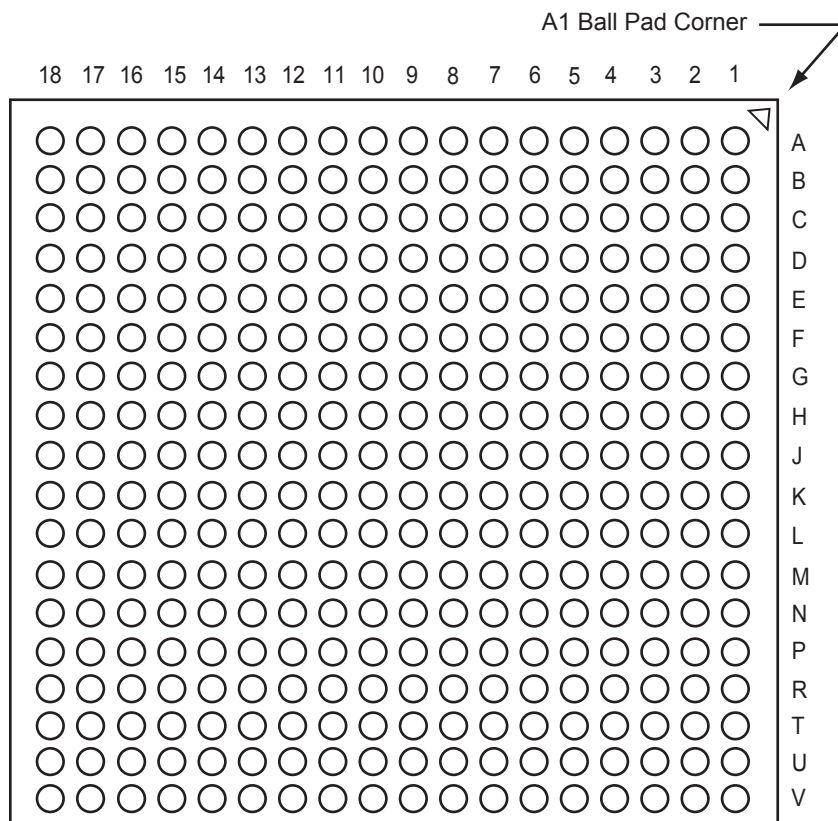


PQ208	
Pin Number	A3PE3000 Function
118	IO134NDB3V2
119	IO134PDB3V2
120	IO132NDB3V2
121	IO132PDB3V2
122	GND
123	VCCIB3
124	GCC2/IO117PSB3V0
125	GCB2/IO116PSB3V0
126	NC
127	IO115NDB3V0
128	GCA2/IO115PDB3V0
129	GCA1/IO114PPB3V0
130	GND
131	VCCPLC
132	GCA0/IO114NPB3V0
133	VCOMPLC
134	GCB0/IO113NDB2V3
135	GCB1/IO113PDB2V3
136	GCC1/IO112PSB2V3
137	IO110NDB2V3
138	IO110PDB2V3
139	IO106PSB2V3
140	VCCIB2
141	GND
142	VCC
143	IO99NDB2V2
144	IO99PDB2V2
145	IO96NDB2V1
146	IO96PDB2V1
147	IO91NDB2V1
148	IO91PDB2V1
149	IO88NDB2V0
150	IO88PDB2V0
151	GBC2/IO84PSB2V0
152	GBA2/IO82PSB2V0
153	GBB2/IO83PSB2V0
154	VMV2
155	GNDQ
156	GND

PQ208	
Pin Number	A3PE3000 Function
157	VMV1
158	GNDQ
159	GBA1/IO81PDB1V4
160	GBA0/IO81NDB1V4
161	GBB1/IO80PDB1V4
162	GND
163	GBB0/IO80NDB1V4
164	GBC1/IO79PDB1V4
165	GBC0/IO79NDB1V4
166	IO74PDB1V4
167	IO74NDB1V4
168	IO70PDB1V3
169	IO70NDB1V3
170	VCCIB1
171	VCC
172	IO56PSB1V1
173	IO55PDB1V1
174	IO55NDB1V1
175	IO54PDB1V1
176	IO54NDB1V1
177	IO40PDB0V4
178	GND
179	IO40NDB0V4
180	IO37PDB0V4
181	IO37NDB0V4
182	IO35PDB0V4
183	IO35NDB0V4
184	IO32PDB0V3
185	IO32NDB0V3
186	VCCIB0
187	VCC
188	IO28PDB0V3
189	IO28NDB0V3
190	IO24PDB0V2
191	IO24NDB0V2
192	IO21PSB0V2
193	IO16PDB0V1
194	IO16NDB0V1
195	GND

PQ208	
Pin Number	A3PE3000 Function
196	IO11PDB0V1
197	IO11NDB0V1
198	IO08PDB0V0
199	IO08NDB0V0
200	VCCIB0
201	GAC1/IO02PDB0V0
202	GAC0/IO02NDB0V0
203	GAB1/IO01PDB0V0
204	GAB0/IO01NDB0V0
205	GAA1/IO00PDB0V0
206	GAA0/IO00NDB0V0
207	GNDQ
208	VMV0

## FG324



*Note:* This is the bottom view of the package.

### Note

For Package Manufacturing and Environmental information, visit the Resource Center at <http://www.microsemi.com/products/fpga-soc/solutions>.

FG324	
Pin Number	A3PE3000 FBGA
A1	GND
A2	IO08NDB0V0
A3	IO08PDB0V0
A4	IO10NDB0V1
A5	IO10PDB0V1
A6	IO12PDB0V1
A7	GND
A8	IO32NDB0V3
A9	IO32PDB0V3
A10	IO42PPB1V0
A11	IO52NPB1V1
A12	GND
A13	IO66NDB1V3
A14	IO72NDB1V3
A15	IO72PDB1V3
A16	IO74NDB1V4
A17	IO74PDB1V4
A18	GND
B1	IO305PDB7V3
B2	GAB2/IO308PDB7V4
B3	GAA0/IO00NPB0V0
B4	VCCIB0
B5	GNDQ
B6	IO12NDB0V1
B7	IO18NDB0V2
B8	VCCIB0
B9	IO42NPB1V0
B10	IO44NDB1V0
B11	VCCIB1
B12	IO52PPB1V1
B13	IO66PDB1V3
B14	GNDQ
B15	VCCIB1
B16	GBA0/IO81NDB1V4
B17	GBA1/IO81PDB1V4
B18	IO88PDB2V0

FG324	
Pin Number	A3PE3000 FBGA
C1	IO305NDB7V3
C2	IO308NDB7V4
C3	GAA2/IO309PPB7V4
C4	GAA1/IO00PPB0V0
C5	VMV0
C6	IO14NDB0V1
C7	IO18PDB0V2
C8	IO40NDB0V4
C9	IO40PDB0V4
C10	IO44PDB1V0
C11	IO56NDB1V1
C12	IO64NDB1V2
C13	IO64PDB1V2
C14	VMV1
C15	GBC0/IO79NDB1V4
C16	GBC1/IO79PDB1V4
C17	GBB2/IO83PPB2V0
C18	IO88NDB2V0
D1	IO303PDB7V3
D2	VCCIB7
D3	GAC2/IO307PPB7V4
D4	IO309NPB7V4
D5	GAB1/IO01PPB0V0
D6	IO14PDB0V1
D7	IO24NDB0V2
D8	IO24PDB0V2
D9	IO28PDB0V3
D10	IO48NDB1V0
D11	IO56PDB1V1
D12	IO60PPB1V2
D13	GBB0/IO80NDB1V4
D14	GBB1/IO80PDB1V4
D15	GBA2/IO82PDB2V0
D16	IO83NPB2V0
D17	VCCIB2
D18	IO90PDB2V1

FG324	
Pin Number	A3PE3000 FBGA
E1	IO303NDB7V3
E2	GNDQ
E3	VMV7
E4	IO307NPB7V4
E5	VCCPLA
E6	GAB0/IO01NPB0V0
E7	VCCIB0
E8	GND
E9	IO28NDB0V3
E10	IO48PDB1V0
E11	GND
E12	VCCIB1
E13	IO60NPB1V2
E14	VCCPLB
E15	IO82NDB2V0
E16	VMV2
E17	GNDQ
E18	IO90NDB2V1
F1	IO299NDB7V3
F2	IO299PDB7V3
F3	IO295PDB7V2
F4	IO295NDB7V2
F5	VCOMPLA
F6	IO291PPB7V2
F7	GAC0/IO02NDB0V0
F8	GAC1/IO02PDB0V0
F9	IO26PDB0V3
F10	IO34PDB0V4
F11	IO58NDB1V2
F12	IO58PDB1V2
F13	IO94PPB2V1
F14	VCOMPLB
F15	GBC2/IO84PDB2V0
F16	IO84NDB2V0
F17	IO92NDB2V1
F18	IO92PDB2V1

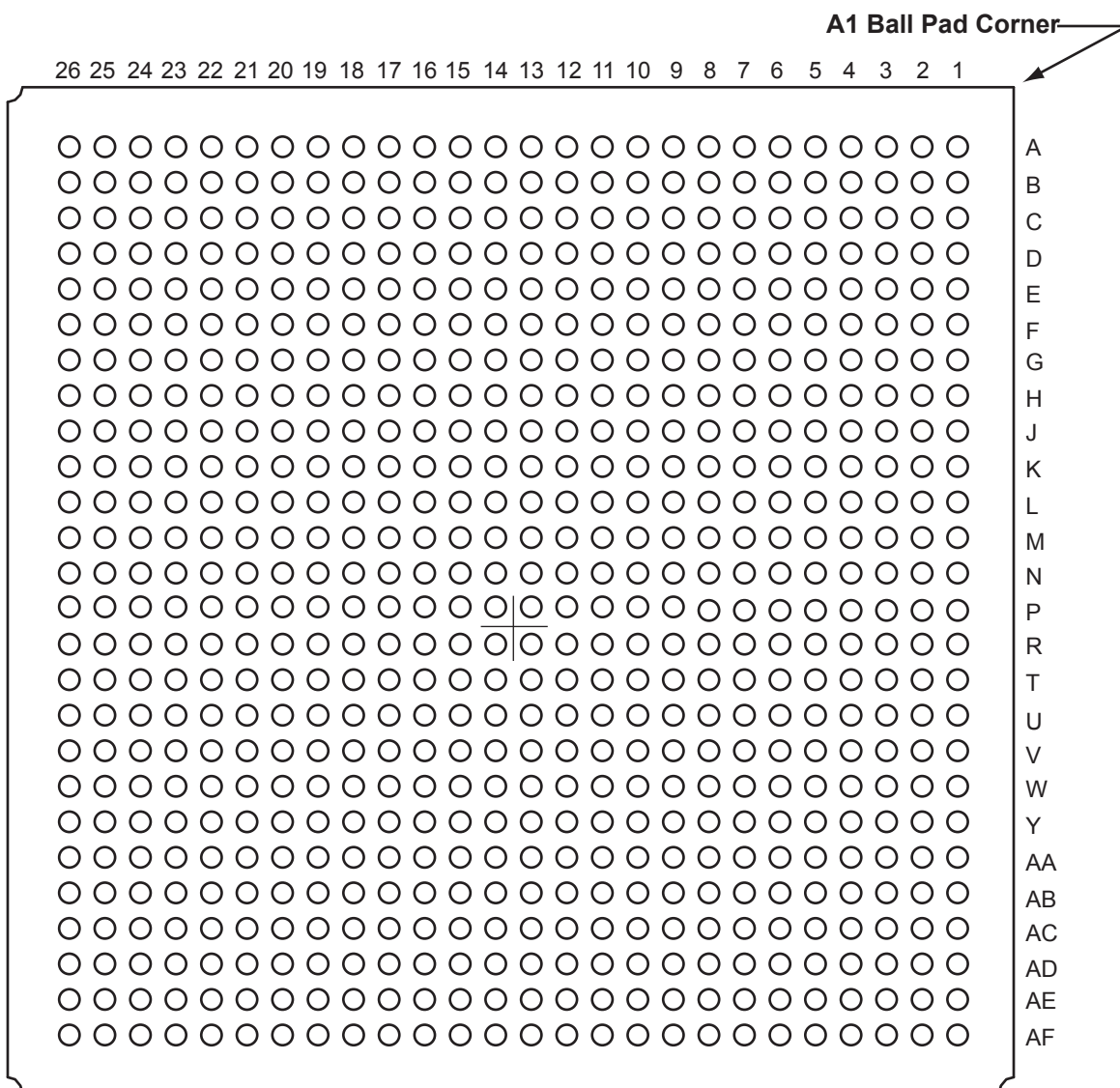
FG484	
Pin Number	A3PE1500 Function
A1	GND
A2	GND
A3	VCCIB0
A4	IO05NDB0V0
A5	IO05PDB0V0
A6	IO11NDB0V1
A7	IO11PDB0V1
A8	IO15PDB0V1
A9	IO17PDB0V2
A10	IO27NDB0V3
A11	IO27PDB0V3
A12	IO32PDB1V0
A13	IO43PDB1V1
A14	IO47NDB1V1
A15	IO47PDB1V1
A16	IO51NDB1V2
A17	IO51PDB1V2
A18	IO54NDB1V3
A19	NC
A20	VCCIB1
A21	GND
A22	GND
AA1	GND
AA2	VCCIB6
AA3	NC
AA4	IO161PDB5V3
AA5	IO155NDB5V2
AA6	IO155PDB5V2
AA7	IO154NDB5V2
AA8	IO154PDB5V2
AA9	IO143PDB5V1
AA10	IO143NDB5V1
AA11	IO131PPB4V2
AA12	IO129NDB4V2
AA13	IO129PDB4V2
AA14	NC

FG484	
Pin Number	A3PE1500 Function
AA15	NC
AA16	IO117NDB4V0
AA17	IO117PDB4V0
AA18	IO115NDB4V0
AA19	IO115PDB4V0
AA20	NC
AA21	VCCIB3
AA22	GND
AB1	GND
AB2	GND
AB3	VCCIB5
AB4	IO159NDB5V3
AB5	IO159PDB5V3
AB6	IO149NDB5V1
AB7	IO149PDB5V1
AB8	IO138NDB5V0
AB9	IO138PDB5V0
AB10	NC
AB11	NC
AB12	IO127NDB4V2
AB13	IO127PDB4V2
AB14	IO125NDB4V1
AB15	IO125PDB4V1
AB16	IO122NDB4V1
AB17	IO122PDB4V1
AB18	NC
AB19	NC
AB20	VCCIB4
AB21	GND
AB22	GND
B1	GND
B2	VCCIB7
B3	NC
B4	IO03NDB0V0
B5	IO03PDB0V0
B6	IO10NDB0V1

FG484	
Pin Number	A3PE1500 Function
B7	IO10PDB0V1
B8	IO15NDB0V1
B9	IO17NDB0V2
B10	IO20PDB0V2
B11	IO29PDB0V3
B12	IO32NDB1V0
B13	IO43NDB1V1
B14	NC
B15	NC
B16	IO53NDB1V2
B17	IO53PDB1V2
B18	IO54PDB1V3
B19	NC
B20	NC
B21	VCCIB2
B22	GND
C1	VCCIB7
C2	NC
C3	NC
C4	NC
C5	GND
C6	IO07NDB0V0
C7	IO07PDB0V0
C8	VCC
C9	VCC
C10	IO20NDB0V2
C11	IO29NDB0V3
C12	NC
C13	NC
C14	VCC
C15	VCC
C16	NC
C17	NC
C18	GND
C19	NC
C20	NC

FG484		FG484		FG484	
Pin Number	A3PE3000 Function	Pin Number	A3PE3000 Function	Pin Number	A3PE3000 Function
H19	IO100PDB2V2	K11	GND	M3	IO272NDB6V4
H20	VCC	K12	GND	M4	GFA2/IO272PDB6V4
H21	VMV2	K13	GND	M5	GFA1/IO273PDB6V4
H22	IO105PDB2V2	K14	VCC	M6	VCCPLF
J1	IO285NDB7V1	K15	VCCIB2	M7	IO271NDB6V4
J2	IO285PDB7V1	K16	GCC1/IO112PPB2V3	M8	GFB2/IO271PDB6V4
J3	VMV7	K17	IO108NDB2V3	M9	VCC
J4	IO279PDB7V0	K18	IO108PDB2V3	M10	GND
J5	IO283PDB7V1	K19	IO110NPB2V3	M11	GND
J6	IO281PDB7V0	K20	IO106NPB2V3	M12	GND
J7	IO287NDB7V1	K21	IO109NDB2V3	M13	GND
J8	VCCIB7	K22	IO107NDB2V3	M14	VCC
J9	GND	L1	IO257PSB6V2	M15	GCB2/IO116PPB3V0
J10	VCC	L2	IO276PDB7V0	M16	GCA1/IO114PPB3V0
J11	VCC	L3	IO276NDB7V0	M17	GCC2/IO117PPB3V0
J12	VCC	L4	GFB0/IO274NPB7V0	M18	VCCPLC
J13	VCC	L5	GFA0/IO273NDB6V4	M19	GCA2/IO115PDB3V0
J14	GND	L6	GFB1/IO274PPB7V0	M20	IO115NDB3V0
J15	VCCIB2	L7	VCOMPLF	M21	IO126PDB3V1
J16	IO84NDB2V0	L8	GFC0/IO275NPB7V0	M22	IO124PSB3V1
J17	IO104NDB2V2	L9	VCC	N1	IO255PPB6V2
J18	IO104PDB2V2	L10	GND	N2	IO253NDB6V2
J19	IO106PPB2V3	L11	GND	N3	VMV6
J20	GNDQ	L12	GND	N4	GFC2/IO270PPB6V4
J21	IO109PDB2V3	L13	GND	N5	IO261PPB6V3
J22	IO107PDB2V3	L14	VCC	N6	IO263PDB6V3
K1	IO277NDB7V0	L15	GCC0/IO112NPB2V3	N7	IO263NDB6V3
K2	IO277PDB7V0	L16	GCB1/IO113PPB2V3	N8	VCCIB6
K3	GNDQ	L17	GCA0/IO114NPB3V0	N9	VCC
K4	IO279NDB7V0	L18	VCOMPLC	N10	GND
K5	IO283NDB7V1	L19	GCB0/IO113NPB2V3	N11	GND
K6	IO281NDB7V0	L20	IO110PPB2V3	N12	GND
K7	GFC1/IO275PPB7V0	L21	IO111NDB2V3	N13	GND
K8	VCCIB7	L22	IO111PDB2V3	N14	VCC
K9	VCC	M1	GNDQ	N15	VCCIB3
K10	GND	M2	IO255NPB6V2	N16	IO116NPB3V0

## FG676



*Note:* This is the bottom view of the package.

### Note

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FG896		FG896		FG896	
Pin Number	A3PE3000 Function	Pin Number	A3PE3000 Function	Pin Number	A3PE3000 Function
A2	GND	AA9	GEB1/IO235PPB6V0	AB15	IO198PDB5V0
A3	GND	AA10	VCC	AB16	IO192NDB4V4
A4	IO14NPB0V1	AA11	IO226PPB5V4	AB17	IO192PDB4V4
A5	GND	AA12	VCCIB5	AB18	IO178NDB4V3
A6	IO07NPB0V0	AA13	VCCIB5	AB19	IO178PDB4V3
A7	GND	AA14	VCCIB5	AB20	IO174NDB4V2
A8	IO09NDB0V1	AA15	VCCIB5	AB21	IO162NPB4V1
A9	IO17NDB0V2	AA16	VCCIB4	AB22	VCC
A10	IO17PDB0V2	AA17	VCCIB4	AB23	VCCPLD
A11	IO21NDB0V2	AA18	VCCIB4	AB24	VCCIB3
A12	IO21PDB0V2	AA19	VCCIB4	AB25	IO150PDB3V4
A13	IO33NDB0V4	AA20	IO174PDB4V2	AB26	IO148PDB3V4
A14	IO33PDB0V4	AA21	VCC	AB27	IO147NDB3V4
A15	IO35NDB0V4	AA22	IO142NPB3V3	AB28	IO145PDB3V3
A16	IO35PDB0V4	AA23	IO144NDB3V3	AB29	IO143PDB3V3
A17	IO41NDB1V0	AA24	IO144PDB3V3	AB30	IO137PDB3V2
A18	IO43NDB1V0	AA25	IO146NDB3V4	AC1	IO254PDB6V2
A19	IO43PDB1V0	AA26	IO146PDB3V4	AC2	IO254NDB6V2
A20	IO45NDB1V0	AA27	IO147PDB3V4	AC3	IO240PDB6V0
A21	IO45PDB1V0	AA28	IO139NDB3V3	AC4	GEC1/IO236PDB6V0
A22	IO57NDB1V2	AA29	IO139PDB3V3	AC5	IO237PDB6V0
A23	IO57PDB1V2	AA30	IO133NDB3V2	AC6	IO237NDB6V0
A24	GND	AB1	IO256NDB6V2	AC7	VCOMPLE
A25	IO69PPB1V3	AB2	IO244PDB6V1	AC8	GND
A26	GND	AB3	IO244NDB6V1	AC9	IO226NPB5V4
A27	GBC1/IO79PPB1V4	AB4	IO241PDB6V0	AC10	IO222NDB5V3
A28	GND	AB5	IO241NDB6V0	AC11	IO216NPB5V2
A29	GND	AB6	IO243NPB6V1	AC12	IO210NPB5V2
AA1	IO256PDB6V2	AB7	VCCIB6	AC13	IO204NDB5V1
AA2	IO248PDB6V1	AB8	VCCPLE	AC14	IO204PDB5V1
AA3	IO248NDB6V1	AB9	VCC	AC15	IO194NDB5V0
AA4	IO246NDB6V1	AB10	IO222PDB5V3	AC16	IO188NDB4V4
AA5	GEA1/IO234PDB6V0	AB11	IO218PPB5V3	AC17	IO188PDB4V4
AA6	GEA0/IO234NDB6V0	AB12	IO206NDB5V1	AC18	IO182PPB4V3
AA7	IO243PPB6V1	AB13	IO206PDB5V1	AC19	IO170NPB4V2
AA8	IO245NDB6V1	AB14	IO198NDB5V0	AC20	IO164NDB4V1

Revision	Changes	Page
Revision 11 (August 2012)	Added a Note stating "VMV pins must be connected to the corresponding VCCI pins. See the "VMVx I/O Supply Voltage (quiet)" section on page 3-1 for further information." to Table 2-1 • Absolute Maximum Ratings and Table 2-2 • Recommended Operating Conditions <sup>1</sup> (SAR 38322).	2-1 3-1 2-1
	The drive strength, IOL, and IOH value for 3.3 V GTL and 2.5 V GTL was changed from 25 mA to 20 mA in the following tables (SAR 31924): "Summary of Maximum and Minimum DC Input and Output Levels" table "Summary of I/O Timing Characteristics—Software Default Settings" table "I/O Output Buffer Maximum Resistances <sup>1</sup> " table "Minimum and Maximum DC Input and Output Levels" table "Minimum and Maximum DC Input and Output Levels" table Also added note stating "Output drive strength is below JEDEC specification" for Tables 2-17 and 2-19. Additionally, the IOL and IOH values for 3.3 V GTL+ and 2.5 V GTL+ were corrected from 51 to 35 (for 3.3 V GTL+) and from 40 to 33 (for 2.5 V GTL+) in table Table 2-13 (SAR 39714).	2-16 2-19 2-20 2-39 2-40
	"Duration of Short Circuit Event Before Failure" table was revised to change the maximum temperature from 110°C to 100°C, with an example of six months instead of three months (SAR 37934).	2-22
	The following sentence was deleted from the "2.5 V LVCMOS" section (SAR 34796): "It uses a 5 V–tolerant input buffer and push-pull output buffer." This change was made in revision 10 and omitted from the change table in error.	2-30
	Figure 2-11 was updated to match tables in the "Summary of I/O Timing Characteristics – Default I/O Software Settings" section (SAR 34889).	2-38
Revision 11 (continued)	In Table 2-81 VIL and VIH were revised so that the maximum is 3.6 V for all listed values of VCCI (SAR 37222).	2-52
	Figure 2-47 and Figure 2-48 are new (SAR 34848).	2-79
	The following sentence was removed from the "VMVx I/O Supply Voltage (quiet)" section in the "Pin Descriptions and Packaging" chapter: "Within the package, the VMV plane is decoupled from the simultaneous switching noise originating from the output buffer VCCI domain" and replaced with "Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks" (SAR 38322). The datasheet mentions that "VMV pins must be connected to the corresponding VCCI pins" for an ESD enhancement.	3-1



Revision	Changes	Page
Advance v0.5 (continued)	The "RESET" section was updated.	2-25
	The "RESET" section was updated.	2-27
	The "Introduction" of the "Introduction" section was updated.	2-28
	PCI-X 3.3 V was added to the Compatible Standards for 3.3 V in Table 2-11 • VCCI Voltages and Compatible Standards	2-29
	Table 2-35 • ProASIC3E I/O Features was updated.	2-54
	The "Double Data Rate (DDR) Support" section was updated to include information concerning implementation of the feature.	2-32
	The "Electrostatic Discharge (ESD) Protection" section was updated to include testing information.	2-35
	Level 3 and 4 descriptions were updated in Table 2-43 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3 Devices.	2-64
	The notes in Table 2-45 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3E Devices were updated.	2-64
	The "Simultaneous Switching Outputs (SSOs) and Printed Circuit Board Layout" section is new.	2-41
	A footnote was added to Table 2-37 • Maximum I/O Frequency for Single-Ended and Differential I/Os in All Banks in ProASIC3E Devices (maximum drive strength and high slew selected).	2-55
	Table 2-48 • ProASIC3E I/O Attributes vs. I/O Standard Applications	2-81
	Table 2-55 • ProASIC3 I/O Standards—SLEW and Output Drive (OUT_DRIVE) Settings	2-85
	The "x" was updated in the "Pin Descriptions" section.	2-50
	The "VCC Core Supply Voltage" pin description was updated.	2-50
	The "VMVx I/O Supply Voltage (quiet)" pin description was updated to include information concerning leaving the pin unconnected.	2-50
	EXTFB was removed from Figure 2-24 • ProASIC3E CCC Options.	2-24
	The CCC Output Peak-to-Peak Period Jitter $F_{CCC\_OUT}$ was updated in Table 2-13 • ProASIC3E CCC/PLL Specification.	2-30
	EXTFB was removed from Figure 2-27 • CCC/PLL Macro.	2-28
	The LVPECL specification in Table 2-45 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3E Devices was updated.	2-64
	Table 2-15 • Levels of Hot-Swap Support was updated.	2-34
	The "Cold-Sparing Support" section was updated.	2-34
	"Electrostatic Discharge (ESD) Protection" section was updated.	2-35
	The VJTAG and I/O pin descriptions were updated in the "Pin Descriptions" section.	2-50
	The "VJTAG JTAG Supply Voltage" pin description was updated.	2-50
	The "VPUMP Programming Supply Voltage" pin description was updated to include information on what happens when the pin is tied to ground.	2-50